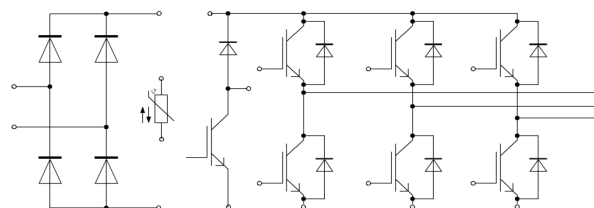
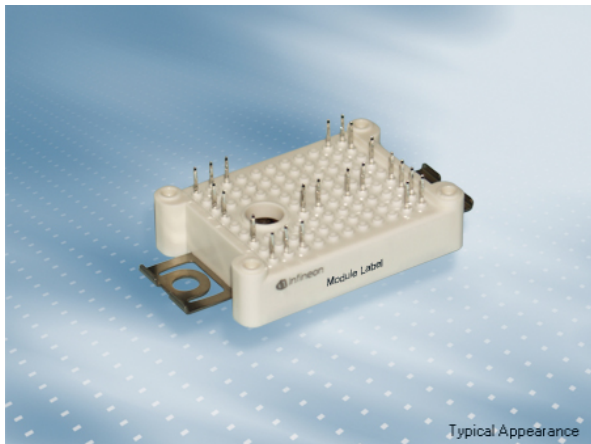


EasyPIM™ 模块 采用第三代沟槽栅/场终止IGBT3和第三代发射极控制二极管 带有温度检测NTC
EasyPIM™ module with Trench/Fieldstop IGBT3 and Emitter Controlled 3 diode and NTC



$V_{CES} = 600V$
 $I_{C\ nom} = 20A / I_{CRM} = 40A$

典型应用

- 辅助逆变器
- 空调
- 电机传动

电气特性

- 低开关损耗
- 低 V_{CEsat}
- 沟槽栅IGBT3
- V_{CEsat} 带正温度系数

机械特性

- 低热阻的三氧化二铝 (Al_2O_3 衬底
- 紧凑型设计
- PressFIT 压接技术
- 集成的安装夹使安装坚固

Typical Applications

- Auxiliary Inverters
- Air Conditioning
- Motor Drives

Electrical Features

- Low Switching Losses
- Low V_{CEsat}
- Trench IGBT 3
- V_{CEsat} with positive Temperature Coefficient

Mechanical Features

- Al_2O_3 Substrate with Low Thermal Resistance
- Compact design
- PressFIT Contact Technology
- Rugged mounting due to integrated mounting clamps

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

| Content of the Code | Digit |
|----------------------------|---------|
| Module Serial Number | 1 - 5 |
| Module Material Number | 6 - 11 |
| Production Order Number | 12 - 19 |
| Datecode (Production Year) | 20 - 21 |
| Datecode (Production Week) | 22 - 23 |

| | | |
|-----------------|---------------------------------|----------------------|
| prepared by: CM | date of publication: 2013-11-25 | |
| approved by: MB | revision: 3.0 | UL approved (E83335) |

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

| | | | | |
|--|--|----------------------------|----------|--------|
| 集电极 - 发射极电压 Collector-emitter voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{CES} | 600 | V |
| 连续集电极直流电流 Continuous DC collector current | $T_C = 95^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ | $I_{C\text{nom}}$ I_C | 20 29 | A A |
| 集电极重复峰值电流 Repetitive peak collector current | $t_P = 1\text{ ms}$ | I_{CRM} | 40 | A |
| 总功率损耗 Total power dissipation | $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ | P_{tot} | 94,0 | W |
| 栅极 - 发射极峰值电压 Gate-emitter peak voltage | | V_{GES} | +/-20 | V |

特征值 / Characteristic Values

| | | | min. | typ. | max. | | |
|---|---|---|--------------------|-------------------------|------|-------------|---|
| 集电极 - 发射极饱和电压 Collector-emitter saturation voltage | $I_C = 20\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 20\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 20\text{ A}, V_{GE} = 15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | $V_{CE\text{sat}}$ | 1,55 1,70 1,80 | 2,00 | V V V | |
| 栅极阈值电压 Gate threshold voltage | $I_C = 0,29\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$ | | V_{GEth} | 4,9 | 5,8 | 6,5 | V |
| 栅极电荷 Gate charge | $V_{GE} = -15\text{ V} \dots +15\text{ V}$ | | Q_G | 0,20 | | | μC |
| 内部栅极电阻 Internal gate resistor | $T_{vj} = 25^{\circ}\text{C}$ | | R_{Gint} | 0,0 | | | Ω |
| 输入电容 Input capacitance | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$ | | C_{ies} | 1,10 | | | nF |
| 反向传输电容 Reverse transfer capacitance | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$ | | C_{res} | 0,034 | | | nF |
| 集电极-发射极截止电流 Collector-emitter cut-off current | $V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{CES} | | | 1,0 | mA |
| 栅极-发射极漏电流 Gate-emitter leakage current | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{GES} | | | 400 | nA |
| 开通延迟时间(电感负载) Turn-on delay time, inductive load | $I_C = 20\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 18\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{don} | 0,02 0,02 0,02 | | | μs μs μs |
| 上升时间(电感负载) Rise time, inductive load | $I_C = 20\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 18\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_r | 0,013 0,016 0,017 | | | μs μs μs |
| 关断延迟时间(电感负载) Turn-off delay time, inductive load | $I_C = 20\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 18\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{doff} | 0,12 0,14 0,15 | | | μs μs μs |
| 下降时间(电感负载) Fall time, inductive load | $I_C = 20\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 18\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_f | 0,07 0,095 0,10 | | | μs μs μs |
| 开通损耗能量(每脉冲) Turn-on energy loss per pulse | $I_C = 20\text{ A}, V_{CE} = 300\text{ V}, L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 1800\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 18\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{on} | 0,32 0,44 0,49 | | | mJ mJ mJ |
| 关断损耗能量(每脉冲) Turn-off energy loss per pulse | $I_C = 20\text{ A}, V_{CE} = 300\text{ V}, L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 4100\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 18\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{off} | 0,44 0,56 0,59 | | | mJ mJ mJ |
| 短路数据 SC data | $V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ | $t_P \leq 8\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 6\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$ | I_{SC} | 140 100 | | | A A |
| 结 - 外壳热阻 Thermal resistance, junction to case | 每个 IGBT / per IGBT | | R_{thJC} | 1,45 | 1,60 | | K/W |
| 外壳 - 散热器热阻 Thermal resistance, case to heatsink | 每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | 1,25 | | | K/W |
| 在开关状态下温度 Temperature under switching conditions | | | $T_{vj\text{op}}$ | -40 | 150 | | $^{\circ}\text{C}$ |

| | |
|-----------------|---------------------------------|
| prepared by: CM | date of publication: 2013-11-25 |
| approved by: MB | revision: 3.0 |

二极管, 逆变器 / Diode, Inverter
最大额定值 / Maximum Rated Values

| | | | | |
|---|--|-----------|--------------|--|
| 反向重复峰值电压 Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 600 | V |
| 连续正向直流电流 Continuous DC forward current | | I_F | 20 | A |
| 正向重复峰值电流 Repetitive peak forward current | $t_P = 1\text{ ms}$ | I_{FRM} | 40 | A |
| I_{2t} -值 I^2t - value | $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I^2t | 49,0 45,0 | A^2s A^2s |

特征值 / Characteristic Values

| | | | min. | typ. | max. | |
|--|---|---|-------------|----------------------|------|---|
| 正向电压 Forward voltage | $I_F = 20\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 20\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 20\text{ A}, V_{GE} = 0\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | V_F | 1,60 1,55 1,50 | 2,00 | V V V |
| 反向恢复峰值电流 Peak reverse recovery current | $I_F = 20\text{ A}, -di_F/dt = 1800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | I_{RM} | 34,0 38,0 40,0 | | A A A |
| 恢复电荷 Recovered charge | $I_F = 20\text{ A}, -di_F/dt = 1800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | Q_r | 1,00 1,75 2,20 | | μC μC μC |
| 反向恢复损耗 (每脉冲) Reverse recovery energy | $I_F = 20\text{ A}, -di_F/dt = 1800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{rec} | 0,21 0,37 0,47 | | mJ mJ mJ |
| 结 - 外壳热阻 Thermal resistance, junction to case | 每个二极管 / per diode | | R_{thJC} | 1,95 | 2,15 | K/W |
| 外壳 - 散热器热阻 Thermal resistance, case to heatsink | 每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | 1,35 | | K/W |
| 在开关状态下温度 Temperature under switching conditions | | | $T_{vj op}$ | -40 | 150 | $^{\circ}\text{C}$ |

二极管, 整流器 / Diode, Rectifier
最大额定值 / Maximum Rated Values

| | | | | |
|---|---|-------------|-------------|--|
| 反向重复峰值电压 Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 800 | V |
| 最大正向均方根电流(每芯片) Maximum RMS forward current per chip | $T_C = 80^{\circ}\text{C}$ | I_{FRMSM} | 50 | A |
| 最大整流器输出均方根电流 Maximum RMS current at rectifier output | $T_C = 80^{\circ}\text{C}$ | I_{RMSM} | 60 | A |
| 正向浪涌电流 Surge forward current | $t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I_{FSM} | 450 360 | A A |
| I_{2t} -值 I^2t - value | $t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I^2t | 1000 640 | A^2s A^2s |

特征值 / Characteristic Values

| | | | min. | typ. | max. | |
|--|---|------------|-------------|------|------|--------------------|
| 正向电压 Forward voltage | $T_{vj} = 150^{\circ}\text{C}, I_F = 20\text{ A}$ | V_F | | 0,85 | | V |
| 反向电流 Reverse current | $T_{vj} = 150^{\circ}\text{C}, V_R = 800\text{ V}$ | I_R | | 0,10 | | mA |
| 结 - 外壳热阻 Thermal resistance, junction to case | 每个二极管 / per diode | R_{thJC} | | 0,95 | 1,05 | K/W |
| 外壳 - 散热器热阻 Thermal resistance, case to heatsink | 每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$ | R_{thCH} | | 0,95 | | K/W |
| 在开关状态下温度 Temperature under switching conditions | | | $T_{vj op}$ | | | $^{\circ}\text{C}$ |

| | |
|-----------------|---------------------------------|
| prepared by: CM | date of publication: 2013-11-25 |
| approved by: MB | revision: 3.0 |

IGBT, 制动-斩波器 / IGBT, Brake-Chopper

最大额定值 / Maximum Rated Values

| | | | | |
|--|--|----------------------------|----------|--------|
| 集电极 - 发射极电压 Collector-emitter voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{CES} | 600 | V |
| 连续集电极直流电流 Continuous DC collector current | $T_C = 95^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ | $I_{C\text{nom}}$ I_C | 20 29 | A A |
| 集电极重复峰值电流 Repetitive peak collector current | $t_P = 1\text{ms}$ | I_{CRM} | 40 | A |
| 总功率损耗 Total power dissipation | $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ | P_{tot} | 94,0 | W |
| 栅极 - 发射极峰值电压 Gate-emitter peak voltage | | V_{GES} | +/-20 | V |

特征值 / Characteristic Values

| | | | min. | typ. | max. | | |
|---|--|---|--------------------|------------------------|------|-------------|---|
| 集电极 - 发射极饱和电压 Collector-emitter saturation voltage | $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | $V_{CE\text{sat}}$ | 1,55 1,70 1,80 | 2,00 | V V V | |
| 栅极阈值电压 Gate threshold voltage | $I_C = 0,29\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$ | | V_{GEth} | 4,9 | 5,8 | 6,5 | V |
| 栅极电荷 Gate charge | $V_{GE} = -15\text{V} \dots +15\text{V}$ | | Q_G | 0,20 | | | μC |
| 内部栅极电阻 Internal gate resistor | $T_{vj} = 25^{\circ}\text{C}$ | | R_{Gint} | 0,0 | | | Ω |
| 输入电容 Input capacitance | $f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$ | | C_{ies} | 1,10 | | | nF |
| 反向传输电容 Reverse transfer capacitance | $f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$ | | C_{res} | 0,034 | | | nF |
| 集电极-发射极截止电流 Collector-emitter cut-off current | $V_{CE} = 600\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{CES} | | | 1,0 | mA |
| 栅极-发射极漏电流 Gate-emitter leakage current | $V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{GES} | | | 400 | nA |
| 开通延迟时间(电感负载) Turn-on delay time, inductive load | $I_C = 20\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 30\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{don} | 0,03 0,03 0,03 | | | μs μs μs |
| 上升时间(电感负载) Rise time, inductive load | $I_C = 20\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 30\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_r | 0,022 0,028 0,03 | | | μs μs μs |
| 关断延迟时间(电感负载) Turn-off delay time, inductive load | $I_C = 20\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 30\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{doff} | 0,20 0,24 0,25 | | | μs μs μs |
| 下降时间(电感负载) Fall time, inductive load | $I_C = 20\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 30\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_f | 0,07 0,11 0,12 | | | μs μs μs |
| 开通损耗能量(每脉冲) Turn-on energy loss per pulse | $I_C = 20\text{A}, V_{CE} = 300\text{V}, L_S = 50\text{nH}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 30\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{on} | 0,45 0,55 0,60 | | | mJ mJ mJ |
| 关断损耗能量(每脉冲) Turn-off energy loss per pulse | $I_C = 20\text{A}, V_{CE} = 300\text{V}, L_S = 50\text{nH}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 30\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{off} | 0,50 0,56 0,60 | | | mJ mJ mJ |
| 短路数据 SC data | $V_{GE} \leq 15\text{V}, V_{CC} = 360\text{V}$ $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$ | $t_P \leq 8\mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 6\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$ | I_{SC} | 140 100 | | | A A |
| 结 - 外壳热阻 Thermal resistance, junction to case | 每个 IGBT / per IGBT | | R_{thJC} | 1,45 | 1,60 | | K/W |
| 外壳 - 散热器热阻 Thermal resistance, case to heatsink | 每个 IGBT / per IGBT $\lambda_{Paste} = 1\text{W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | 1,25 | | | K/W |
| 在开关状态下温度 Temperature under switching conditions | | | $T_{vj\text{op}}$ | -40 | 150 | | $^{\circ}\text{C}$ |

| | |
|-----------------|---------------------------------|
| prepared by: CM | date of publication: 2013-11-25 |
| approved by: MB | revision: 3.0 |



二极管，制动-斩波器 / Diode, Brake-Chopper
最大额定值 / Maximum Rated Values

| | | | | |
|---|--|-----------|--------------|--|
| 反向重复峰值电压 Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 600 | V |
| 连续正向直流电流 Continuous DC forward current | | I_F | 10 | A |
| 正向重复峰值电流 Repetitive peak forward current | $t_P = 1\text{ ms}$ | I_{FRM} | 20 | A |
| I_{2t} -值 I_{2t} -value | $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I_{2t} | 12,5 9,50 | A^2s A^2s |

特征值 / Characteristic Values

| | | | min. | typ. | max. | |
|--|---|---|--------------------|----------------------|------|---|
| 正向电压 Forward voltage | $I_F = 10\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 10\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 10\text{ A}, V_{GE} = 0\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | V_F | 1,60 1,55 1,50 | 2,00 | V V V |
| 反向恢复峰值电流 Peak reverse recovery current | $I_F = 10\text{ A}, -di_F/dt = 1500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | I_{RM} | 18,0 19,0 21,0 | | A A A |
| 恢复电荷 Recovered charge | $I_F = 10\text{ A}, -di_F/dt = 1500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | Q_r | 0,50 0,85 1,10 | | μC μC μC |
| 反向恢复损耗 (每脉冲) Reverse recovery energy | $I_F = 10\text{ A}, -di_F/dt = 1500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{rec} | 0,11 0,20 0,26 | | mJ mJ mJ |
| 结 - 外壳热阻 Thermal resistance, junction to case | 每个二极管 / per diode | | R_{thJC} | 2,90 | 3,20 | K/W |
| 外壳 - 散热器热阻 Thermal resistance, case to heatsink | 每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | 1,40 | | K/W |
| 在开关状态下温度 Temperature under switching conditions | | | $T_{vj\text{ op}}$ | -40 | 150 | $^{\circ}\text{C}$ |

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

| | | | min. | typ. | max. | |
|------------------------------|---|--|--------------|------|------|------------------|
| 额定电阻值 Rated resistance | $T_C = 25^{\circ}\text{C}$ | | R_{25} | 5,00 | | $\text{k}\Omega$ |
| R100 偏差 Deviation of R100 | $T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$ | | $\Delta R/R$ | -5 | 5 | % |
| 耗散功率 Power dissipation | $T_C = 25^{\circ}\text{C}$ | | P_{25} | | 20,0 | mW |
| B-值 B-value | $R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/50}$ | 3375 | | K |
| B-值 B-value | $R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/80}$ | 3411 | | K |
| B-值 B-value | $R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/100}$ | 3433 | | K |

根据应用手册标定

Specification according to the valid application note.

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模块 / Module

| | | | | | |
|---|--|--|--------------------------------|--------------|--------|
| 绝缘测试电压 Isolation test voltage | RMS, f = 50 Hz, t = 1 min. | V _{ISOL} | 2,5 | | kV |
| 内部绝缘 Internal isolation | 基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140) | | Al ₂ O ₃ | | |
| 爬电距离 Creepage distance | 端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal | | 11,5 6,3 | | mm |
| 电气间隙 Clearance | 端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal | | 10,0 5,0 | | mm |
| 相对电痕指数 Comperative tracking index | | CTI | > 200 | | |
| | | | min. | typ. | max. |
| 杂散电感,模块 Stray inductance module | | L _{sCE} | | 30 | nH |
| 模块引线电阻,端子-芯片 Module lead resistance, terminals - chip | T _c = 25°C, 每个开关 / per switch | R _{CC'+EE'} R _{AA'+CC'} | | 8,00 4,00 | mΩ |
| 储存温度 Storage temperature | | T _{stg} | -40 | | 125 °C |
| Anpresskraft für mech. Bef. pro Feder mounting force per clamp | | F | 20 | - | 50 N |
| 重量 Weight | | G | | 24 | g |

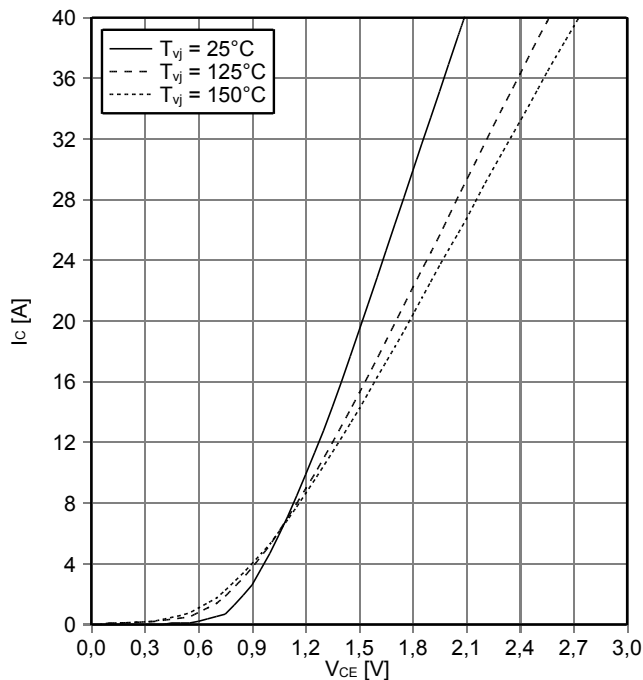
Der Strom im Dauerbetrieb ist auf 25 A effektiv pro Anschlusspin begrenzt
The current under continuous operation is limited to 25 A rms per connector pin

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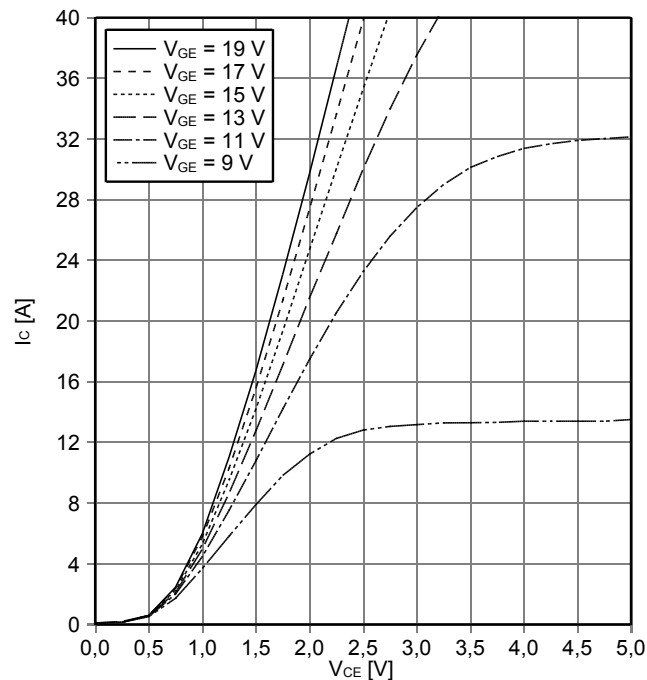
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



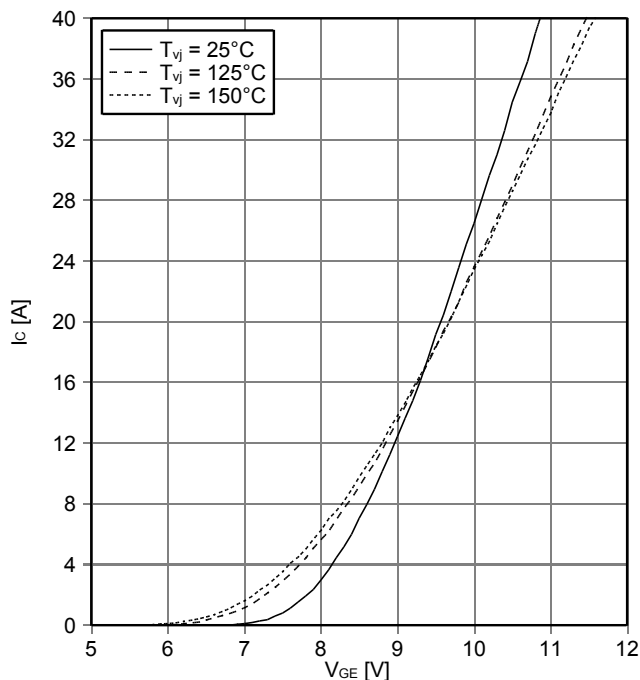
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



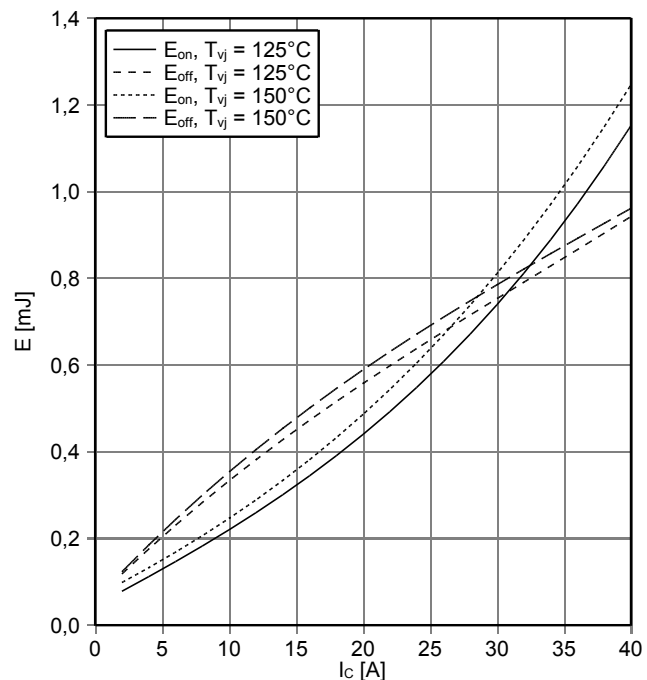
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 18\ \Omega$, $R_{Goff} = 18\ \Omega$, $V_{CE} = 300\text{ V}$

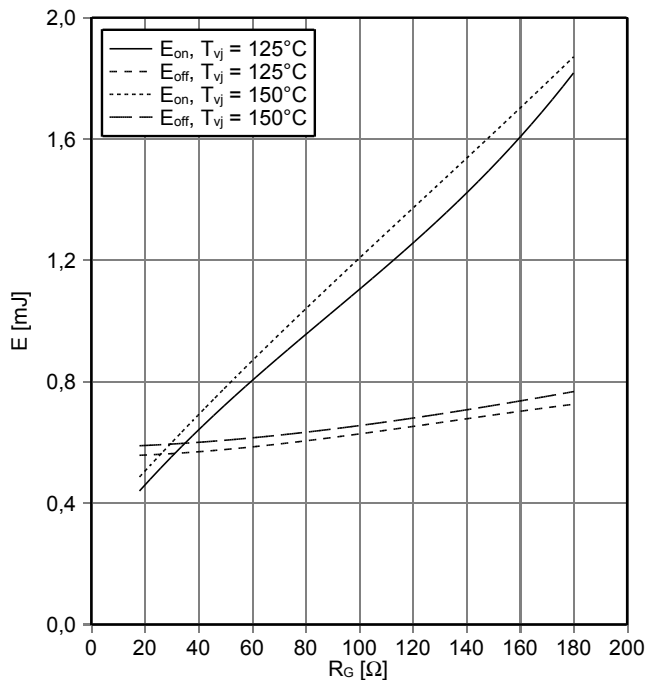


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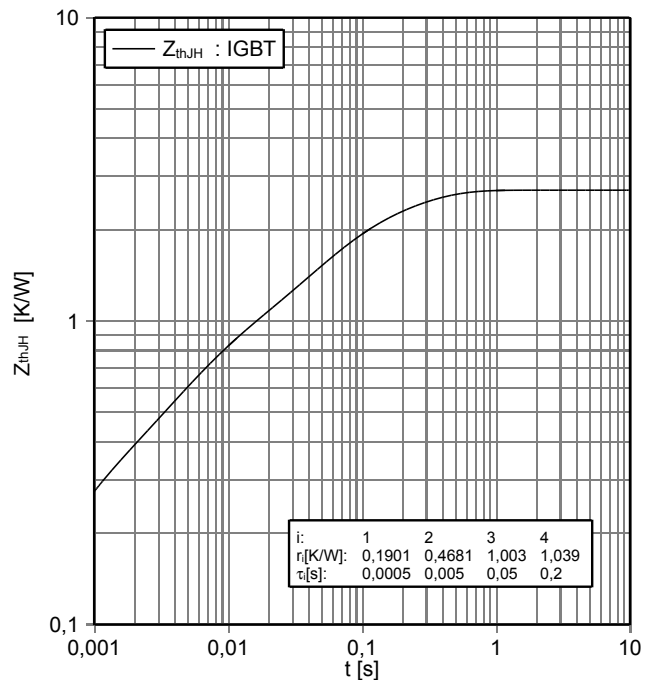
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 20\text{ A}, V_{CE} = 300\text{ V}$



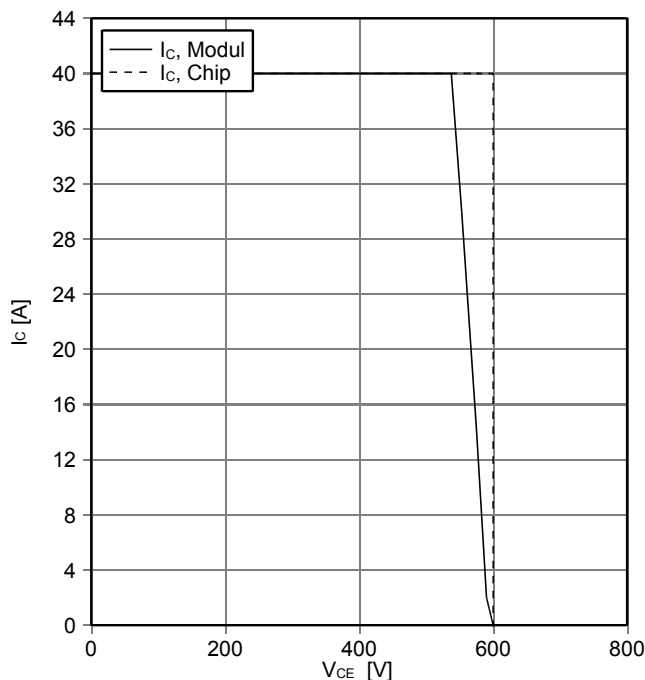
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter

$Z_{thJH} = f(t)$



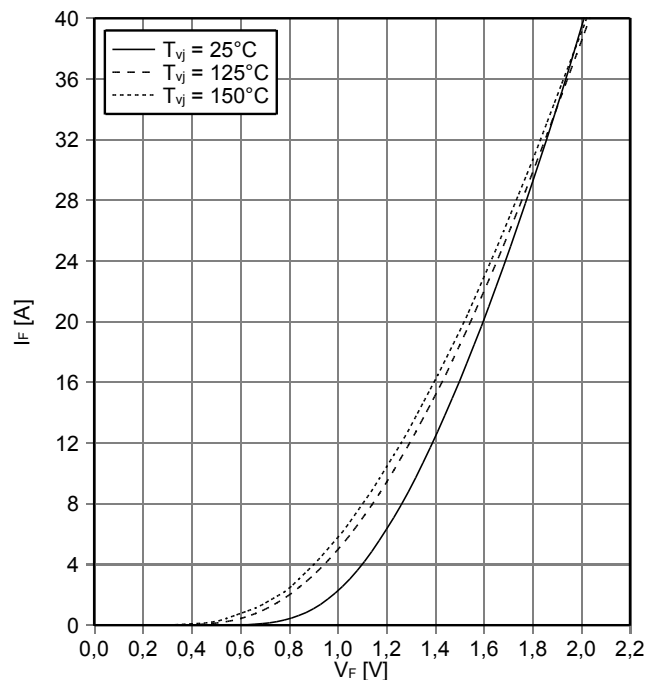
反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 18\ \Omega, T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 逆变器 (典型)
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$

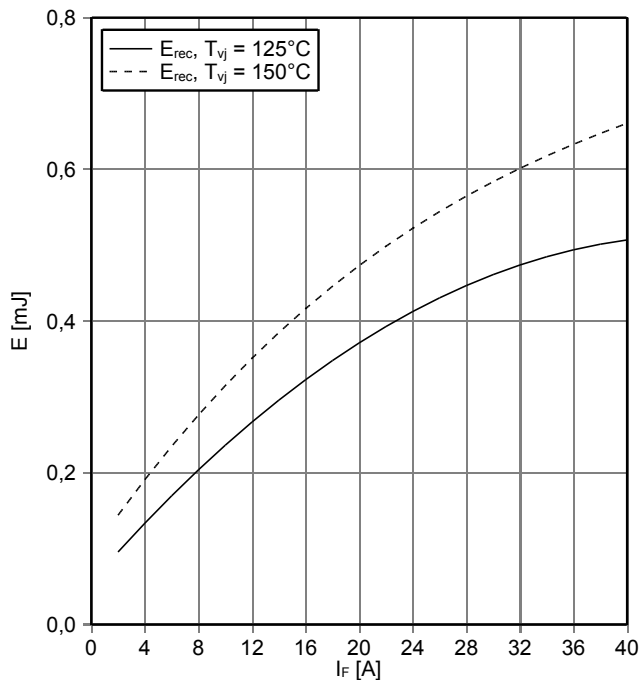


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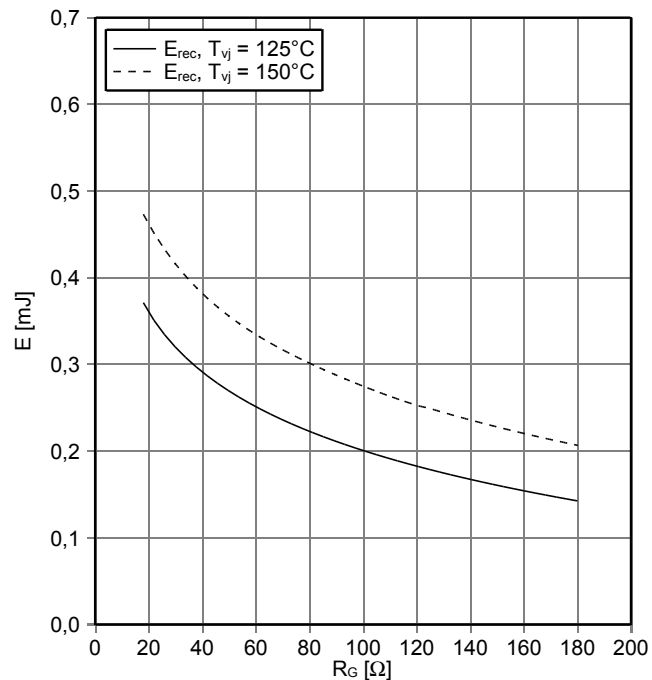
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 18 \Omega, V_{CE} = 300 V$



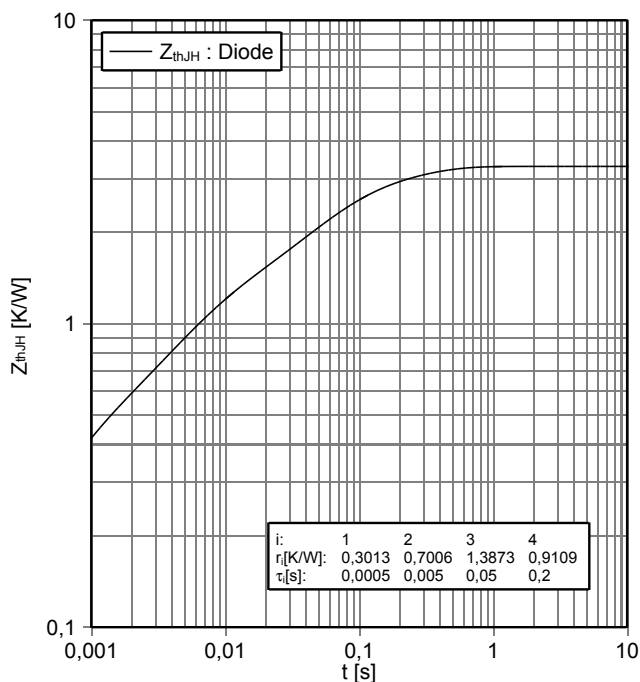
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 20 A, V_{CE} = 300 V$



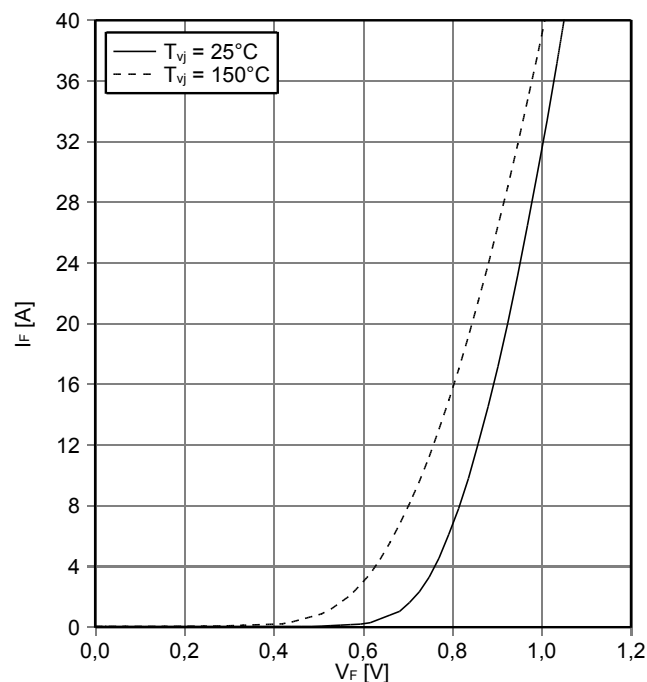
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter

$Z_{thJH} = f(t)$



正向偏压特性 二极管,整流器 (典型)
forward characteristic of Diode, Rectifier (typical)

$I_F = f(V_F)$

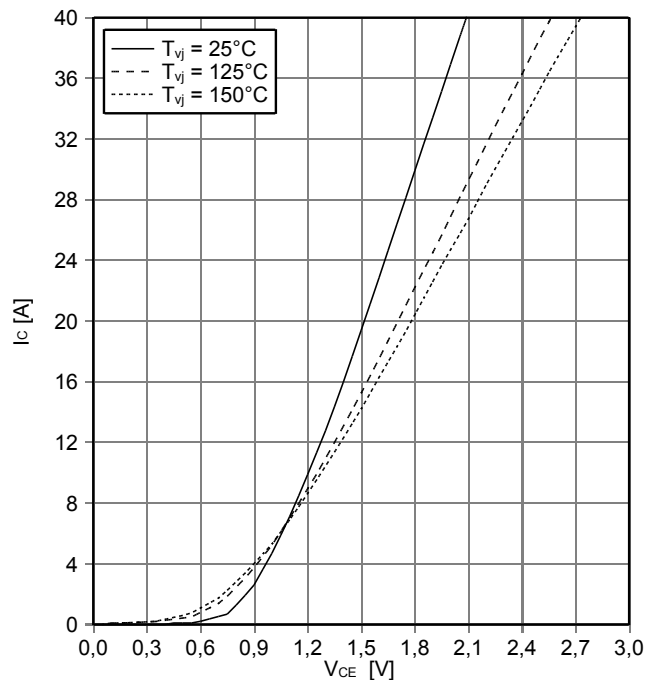


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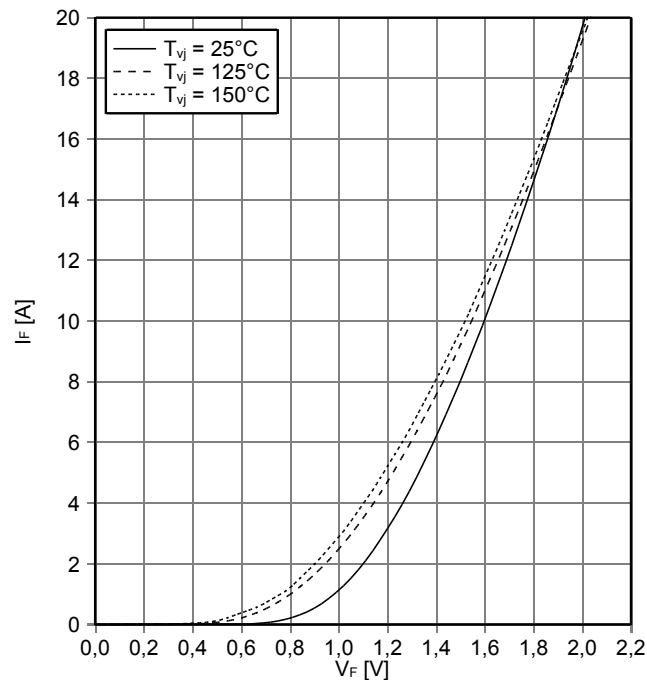
输出特性 IGBT, 制动-斩波器 (典型)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



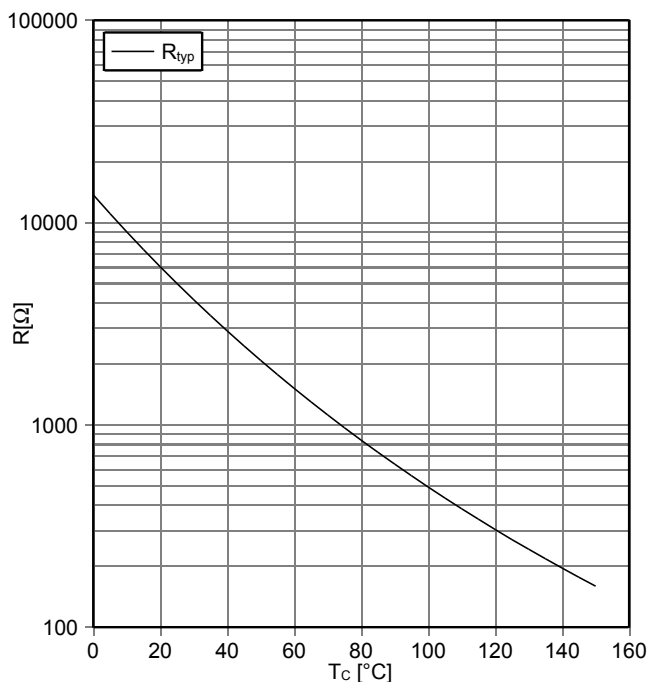
正向偏压特性 二极管, 制动-斩波器 (典型)
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$



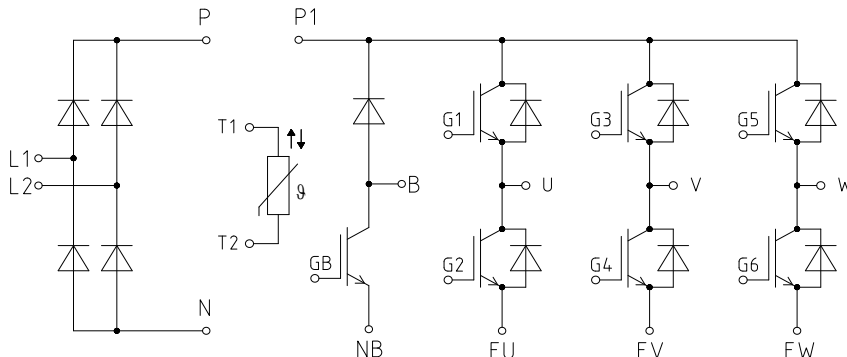
负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)

$R = f(T)$

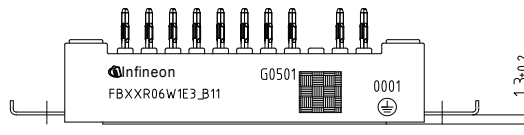
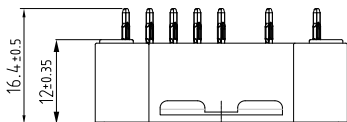


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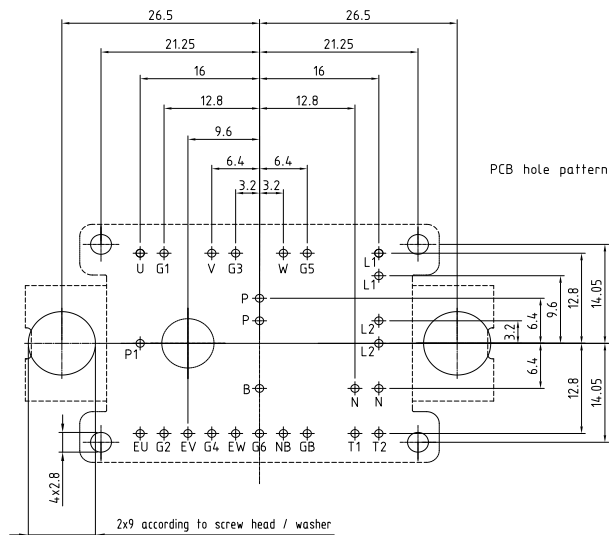
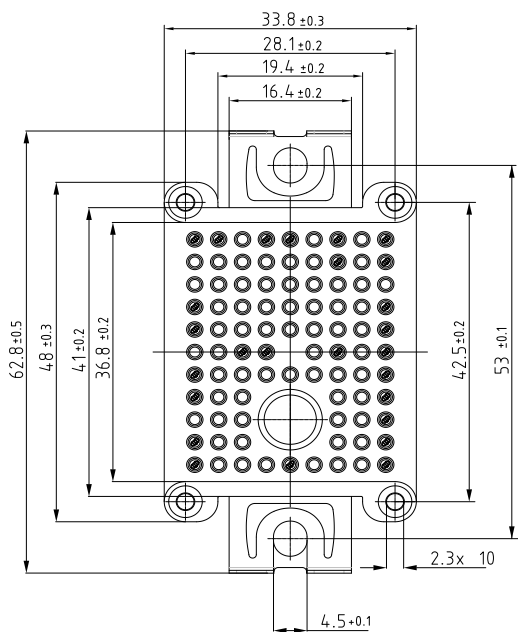
接线图 / circuit_diagram_headline



封装尺寸 / package outlines



- Pin-Grid 3.2mm
- Tolerance of PCB hole pattern $\oplus \phi 0.1$
- Hole specification for contacts see AN 2009-01
- Diameters of drill $\phi 1.15$ mm and copper thickness in hole 25-50 μ m



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